

Title (en)

METHOD OF FORMING A TANTALUM-CONTAINING LAYER ON A SUBSTRATE

Title (de)

VERFAHREN ZUR BILDUNG EINER TANTALUMHALTIGEN SCHICHT AUF EINEM SUBSTRAT

Title (fr)

PROCÉDÉ DE FORMATION D'UNE COUCHE CONTENANT DU TANTALE SUR UN SUBSTRAT

Publication

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Application

EP 09780636 A 20090715

Priority

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Abstract (en)

[origin: WO2010012595A1] A method for forming a tantalum-containing layer on a substrate, the method comprising at least the steps of: a) providing a vapor comprising at least one precursor compound of the formula $Cp(R_1)_m Ta(NR_2)_2(=NR_3)$ (I); Wherein: R_1 is an organic ligand, each one independently selected in the group consisting of H, linear or branched hydrocarbyl radical comprising from 1 to 6 carbon atoms; R_2 is an organic ligand, each one independently selected in the group consisting of H, linear or branched hydrocarbyl radical comprising from 1 to 6 carbon atoms; R_3 is an organic ligand selected in the group consisting of H, linear or branched hydrocarbyl radical comprising from 1 to 6 carbon atoms; b) reacting the vapor comprising the at least one compound of formula (I) with the substrate, according to an atomic layer deposition process, to form a layer of a tantalum-containing complex on at least one surface of said substrate.

IPC 8 full level

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CPC (source: EP KR US)

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